

EAST: [10613412 EEPROM 2T: cell.wsp:1]

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DBs: USPAT.US PGPUB: EPO: JPO: DERWENT: IBM: TDB

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May 2004

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U	I	Investor	Document	Issue	P	Title	Current	Current	XR	Retrieval	S	C	P	Image	Doc	P
1	<input type="checkbox"/>	Ono, Takashi	US 4884239	1989	1	Method for erasing data in a semiconductor	365/185	365/185	09		F	F	F	F	US 488423	F
2	<input type="checkbox"/>	Sato, Nobuyu	US 4881201	1989	1	Semiconductor integrated circuit device	365/185	365/185	06		F	F	F	F	US 488120	F
3	<input type="checkbox"/>	Hsieh, Ning e	US 4878101	1989	1	Single transistor cell for electrically-erasable	365/185	257/E28	30		F	F	F	F	US 487810	F
4	<input type="checkbox"/>	Jungroth, Ow	US 4875188	1989	8	Voltage margining circuit for flash eeprom	365/185	307/28			F	F	F	F	US 487518	F
5	<input type="checkbox"/>	Kreifels, Jerr	US 4860261	1989	7	Leakage verification for flash EPROM	365/185	365/185	22		F	F	F	F	US 486026	F
6	<input type="checkbox"/>	Terada, Yasu	US 4858194	1989	1	Nonvolatile semiconductor memory device us	365/185	365/185	23		F	F	F	F	US 485819	F
7	<input type="checkbox"/>	Jungroth, Ow	US 4858186	1989	6	A circuit for providing a load for the charging	365/185	365/185	104		F	F	F	F	US 485818	F
8	<input type="checkbox"/>	Mitchell, Alla	US 4853895	1989	8	EEPROM including programming electrode ex	365/185	257/320			F	F	F	F	US 485389	F
9	<input type="checkbox"/>	McNutt, Mic	US 4852063	1989	8	Programmable voltage offset circuit	365/185	365/185	03		F	F	F	F	US 485206	F
10	<input type="checkbox"/>	Kreifels, Jerr	US 4841482	1989	5	Leakage verification for flash EPROM	365/185	365/185	18		F	F	F	F	US 484148	F

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